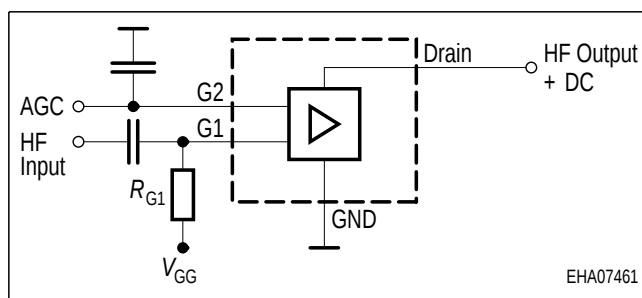
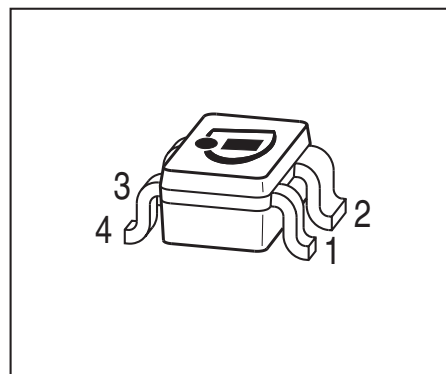


Silicon N-Channel MOSFET Tetrode

- Designed for input stages of UHF- and VHF-tuners with AGC function
- Supporting 5 V operations and power saving 3 V operations
- Integrated ESD gate protection diodes
- Very low noise figure
- High gain, high forward transadmittance
- Very good cross modulation at gain reduction
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Package	Pin Configuration						Marking
BF5030	SOT143	1=S	2=D	3=G2	4=G1	-	-	KXs
BF5030R	SOT143R	1=D	2=S	3=G1	4=G2	-	-	KXs
BF5030W	SOT343	1=D	2=S	3=G1	4=G2	-	-	KXs

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	8	V
Continuous drain current	I_D	25	mA
Gate 1/ gate 2-source current	I_{G1S}, I_{G2S}	± 1	mA
Gate 1/ gate 2-source voltage	V_{G1S}, V_{G2S}	± 6	V
Total power dissipation	P_{tot}		mW
$T_S \leq 94\text{ °C}$, BF5030W		200	
$T_S \leq 76\text{ °C}$, BF5030, BF5030R		200	
Storage temperature	T_{stg}	-55 ... 150	°C
Channel temperature	T_{ch}	150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Channel - soldering point ¹⁾	R_{thchs}		K/W
BF5030W		≤ 280	
BF5030, BF5030R		≤ 370	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

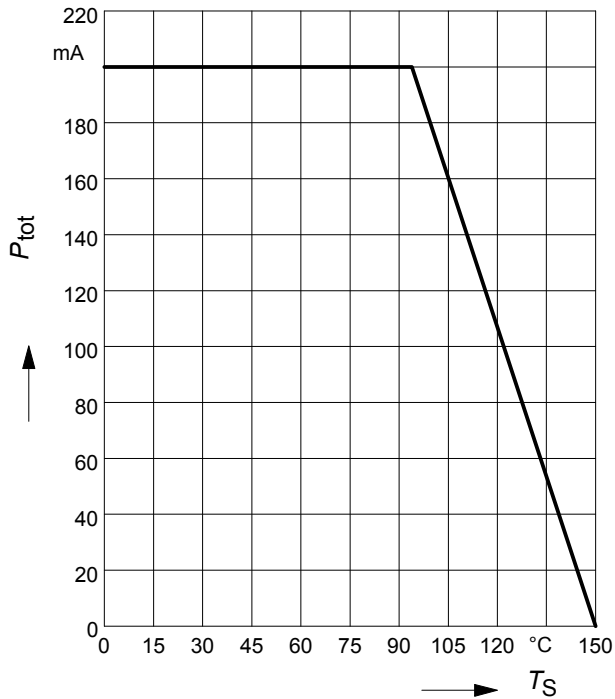
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Drain-source breakdown voltage $I_D = 20\ \mu\text{A}$, $V_{G1S} = 0$, $V_{G2S} = 0$	$V_{(BR)DS}$	12	-	-	V
Gate1-source breakdown voltage $+I_{G1S} = 10\ \text{mA}$, $V_{G2S} = 0$, $V_{DS} = 0$	$+V_{(BR)G1SS}$	6	-	15	
Gate2-source breakdown voltage $+I_{G2S} = 10\ \text{mA}$, $V_{G1S} = 0$, $V_{DS} = 0$	$+V_{(BR)G2SS}$	6	-	15	
Gate1-source leakage current $V_{G1S} = 6\ \text{V}$, $V_{G2S} = 0$, $V_{DS} = 0$	$+I_{G1SS}$	-	-	50	nA
Gate2-source leakage current $V_{G2S} = 6\ \text{V}$, $V_{G1S} = 0$, $V_{DS} = 0$	$+I_{G2SS}$	-	-	50	
Drain current $V_{DS} = 3\ \text{V}$, $V_{G1S} = 0$, $V_{G2S} = 3\ \text{V}$ $V_{DS} = 5\ \text{V}$, $V_{G1S} = 0$, $V_{G2S} = 4\ \text{V}$	I_{DSS}	- -	- -	100 100	
Drain-source current $V_{DS} = 3\ \text{V}$, $V_{G2S} = 3\ \text{V}$, $R_{G1} = 82\ \text{k}\Omega$ $V_{DS} = 5\ \text{V}$, $V_{G2S} = 4\ \text{V}$, $R_{G1} = 180\ \text{k}\Omega$	I_{DSX}	- -	13 13	- -	mA
Gate1-source pinch-off voltage $V_{DS} = 3\ \text{V}$, $V_{G2S} = 3\ \text{V}$, $I_D = 20\ \mu\text{A}$ $V_{DS} = 5\ \text{V}$, $V_{G2S} = 4\ \text{V}$, $I_D = 20\ \mu\text{A}$	$V_{G1S(p)}$	- -	0.7 0.7	- -	
Gate2-source pinch-off voltage $V_{DS} = 3\ \text{V}$, $V_{G1S} = 3\ \text{V}$, $I_D = 20\ \mu\text{A}$ $V_{DS} = 5\ \text{V}$, $V_{G1S} = 4\ \text{V}$, $I_D = 20\ \mu\text{A}$	$V_{G2S(p)}$	- -	0.7 0.7	- -	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics - (verified by random sampling)					
Forward transconductance $V_{DS} = 3\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 3\text{ V}$ $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$	g_{fs}	- -	41 41	- -	mS
Gate1 input capacitance $V_{DS} = 3\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 3\text{ V}$ $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$	C_{g1ss}	- -	2.7 2.8	- -	pF
Output capacitance $V_{DS} = 3\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 3\text{ V}$ $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$	C_{dss}	- -	1.6 1.5	- -	
Power gain $V_{DS} = 3\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 3\text{ V}$, $f = 800\text{ MHz}$ $V_{DS} = 3\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 3\text{ V}$, $f = 45\text{ MHz}$ $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$, $f = 800\text{ MHz}$ $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$, $f = 45\text{ MHz}$	G_p	- - - -	24 34 24 34	- - - -	
Noise figure $V_{DS} = 3\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 3\text{ V}$, $f = 800\text{ MHz}$ $V_{DS} = 3\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 3\text{ V}$, $f = 45\text{ MHz}$ $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$, $f = 800\text{ MHz}$ $V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $V_{G2S} = 4\text{ V}$, $f = 45\text{ MHz}$	F	- - - -	1.3 0.9 1.3 0.9	- - - -	dB
Gain control range $V_{DS} = 3\text{ V}$, $V_{G2S} = 3...0\text{ V}$, $f = 800\text{ MHz}$ $V_{DS} = 5\text{ V}$, $V_{G2S} = 4...0\text{ V}$, $f = 800\text{ MHz}$	ΔG_p	45 45	50 50	- -	
Cross-modulation $k=1\%$, $f_w=50\text{MHz}$, $f_{unw}=60\text{MHz}$ AGC = 0 AGC = 10 dB AGC = 40 dB	X_{mod}	90 - 96	94 92 98	- - -	

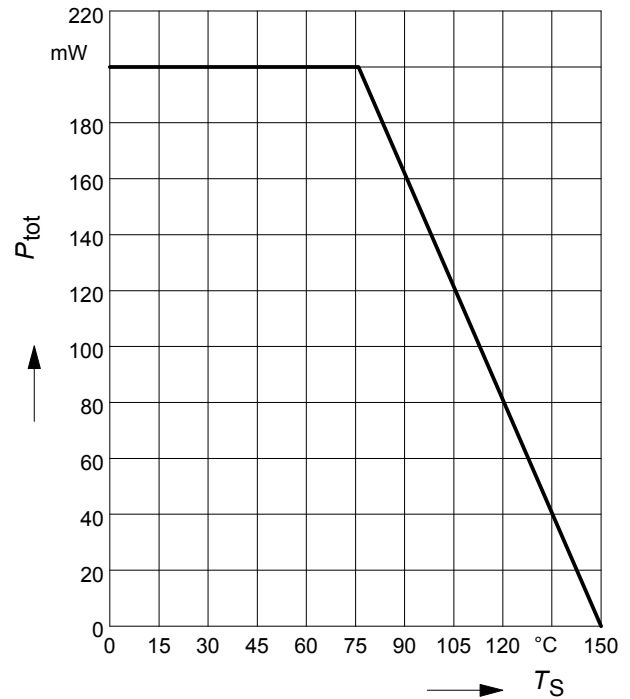
Total power dissipation $P_{\text{tot}} = f(T_S)$

BF5030W



Total power dissipation $P_{\text{tot}} = f(T_S)$

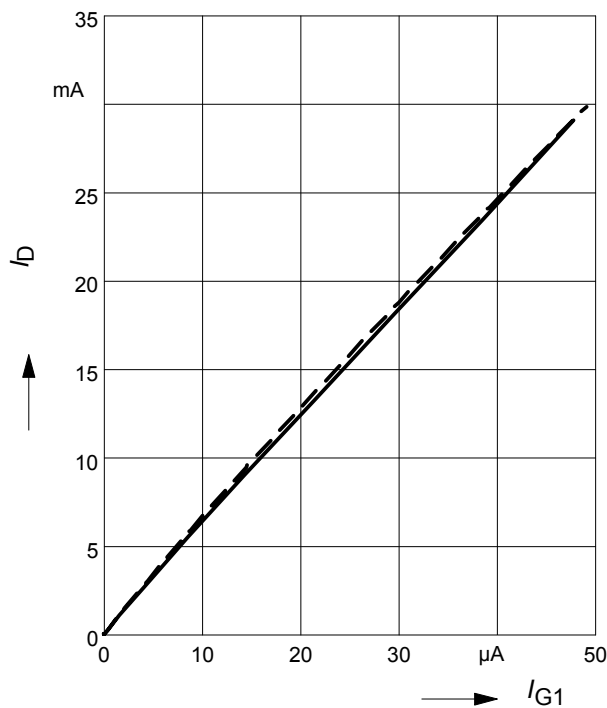
BF5030, BF5030R



Drain current $I_D = f(I_{G1})$

— $V_{DS} = 3 \text{ V}$, $V_{G2S} = 3 \text{ V}$

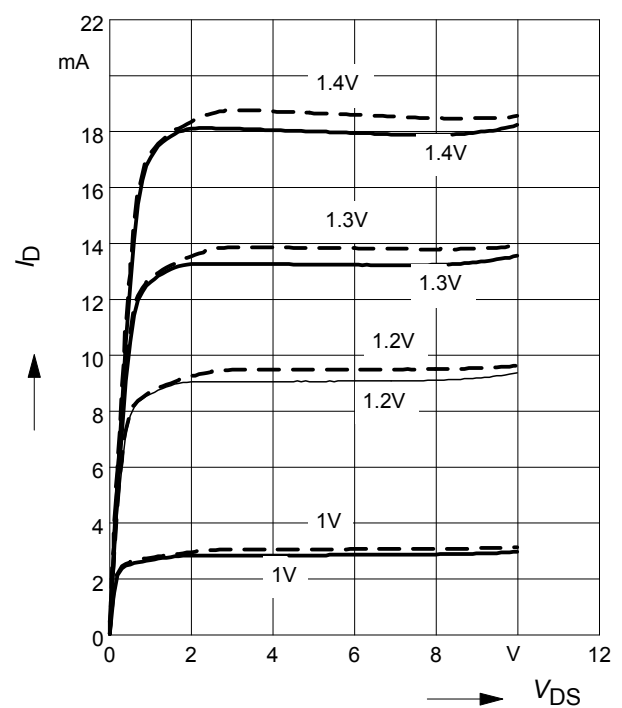
... $V_{DS} = 5 \text{ V}$, $V_{G2S} = 4 \text{ V}$



Output characteristics $I_D = f(V_{DS})$

$V_{G1S} = \text{Parameter}$

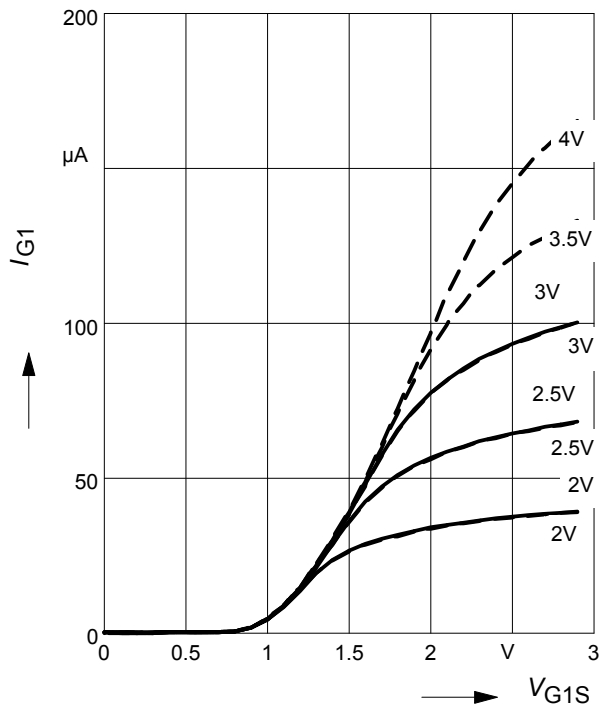
— $V_{DS} = 3 \text{ V}$, ... $V_{DS} = 5 \text{ V}$



Gate 1 current $I_{G1} = f(V_{G1S})$

$V_{G2S} = \text{Parameter}$

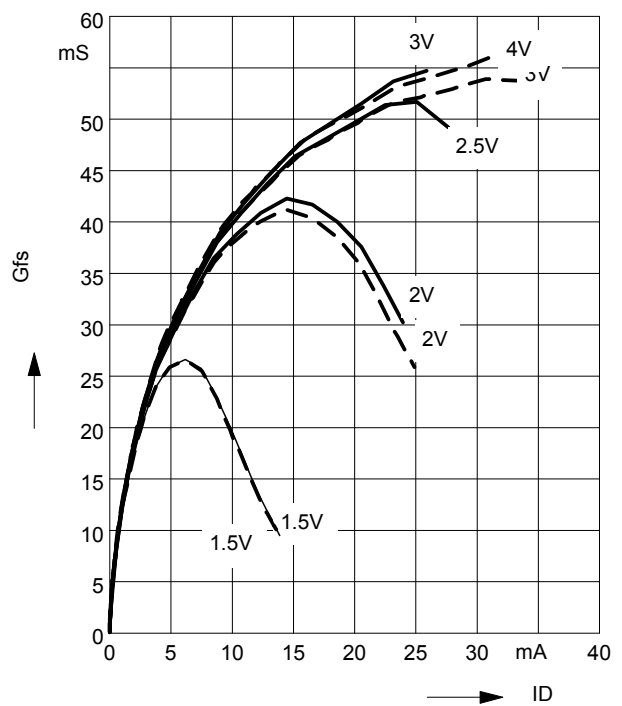
— $V_{DS} = 3 \text{ V}$, ... $V_{DS} = 5 \text{ V}$



Gate 1 forward transconductance

$g_{fs} = f(I_D), V_{G2S} = \text{Parameter}$

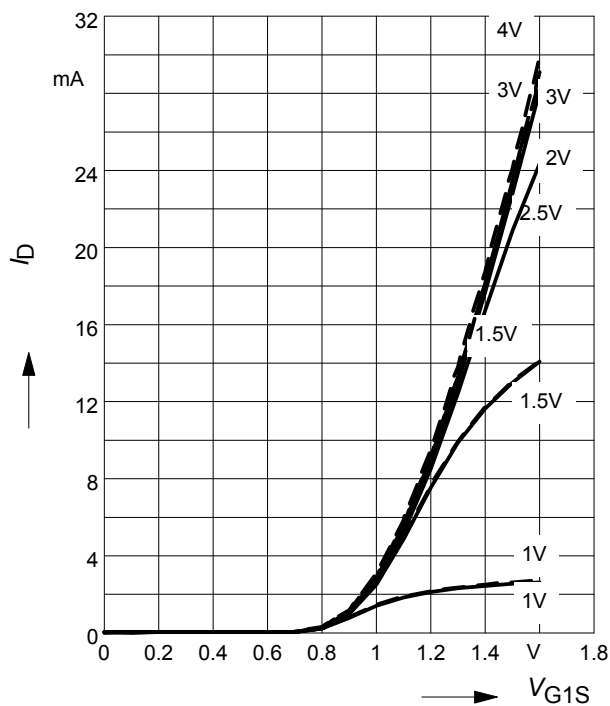
— $V_{DS} = 3 \text{ V}$, ... $V_{DS} = 5 \text{ V}$



Drain current $I_D = f(V_{G1S})$

$V_{G2S} = \text{Parameter}$

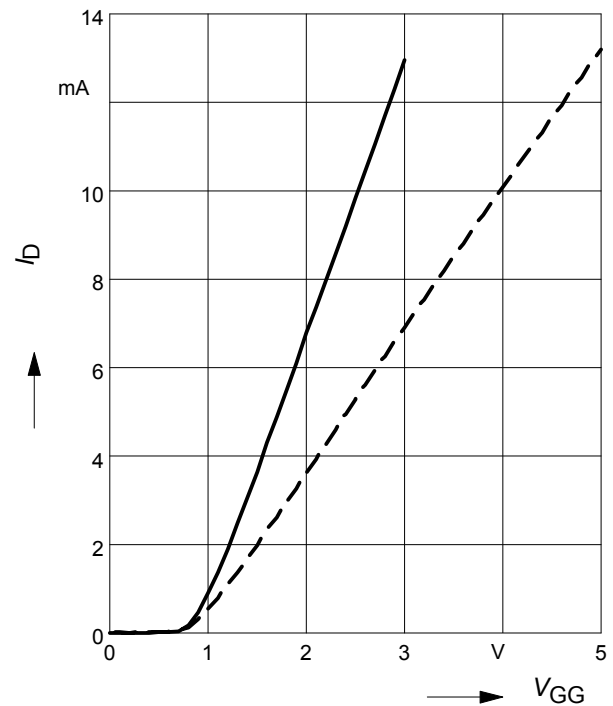
— $V_{DS} = 3 \text{ V}$, ... $V_{DS} = 5 \text{ V}$



Drain current $I_D = f(V_{GG})$

— $V_{DS} = 3 \text{ V}$, $V_{G2S} = 3 \text{ V}$, $R_{G1} = 82 \text{ k}\Omega$

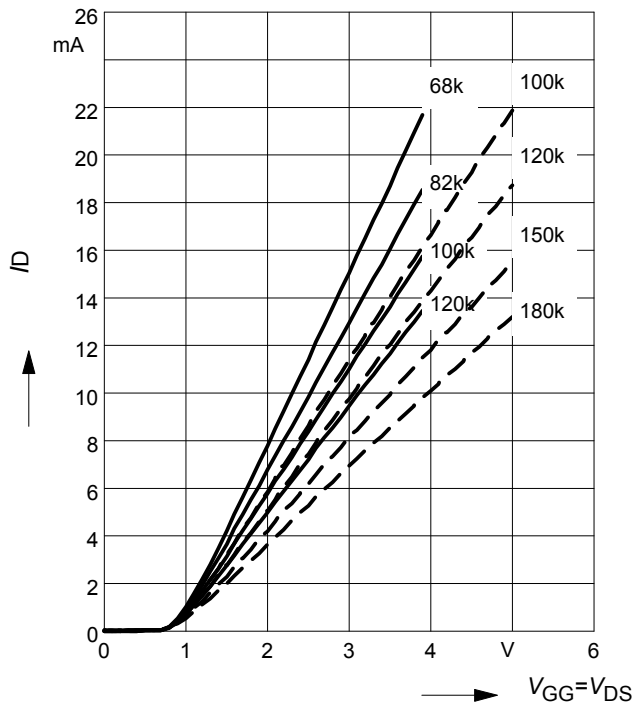
... $V_{DS} = 5 \text{ V}$, $V_{G2S} = 4 \text{ V}$, $R_{G1} = 180 \text{ k}\Omega$



Drain current $I_D = f(V_{GG})$

R_{G1} = Parameter in k Ω

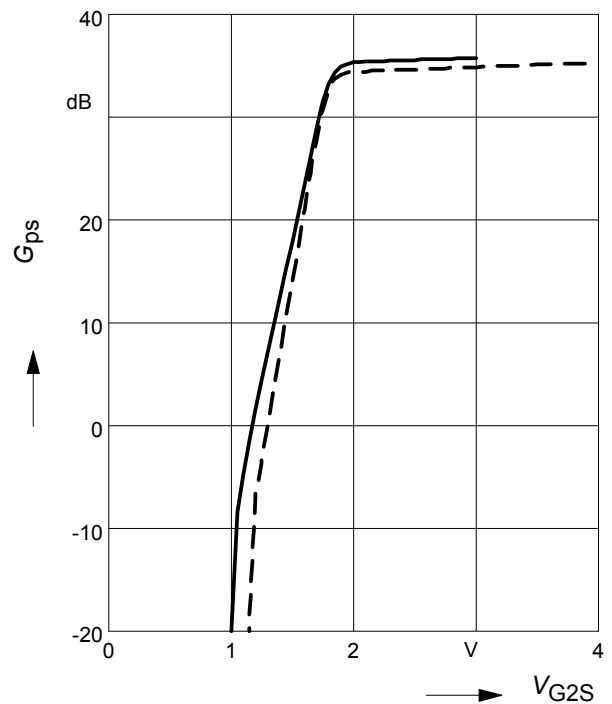
— $V_{DS} = 3$ V, ... $V_{DS} = 5$ V



Power gain $G_{ps} = f(V_{G2S}), f = 45$ MHz

— $V_{DS} = 3$ V, $V_{G2S} = 3$ V, $R_{G1} = 82$ k Ω

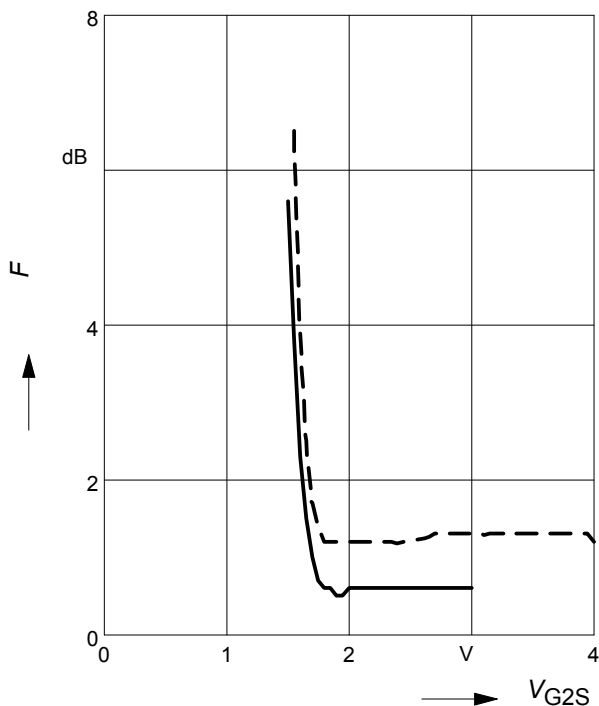
... $V_{DS} = 5$ V, $V_{G2S} = 4$ V, $R_{G1} = 180$ k Ω



Noise figure $F = f(V_{G2S}), f = 45$ MHz

— $V_{DS} = 3$ V, $V_{G2S} = 3$ V, $R_{G1} = 82$ k Ω

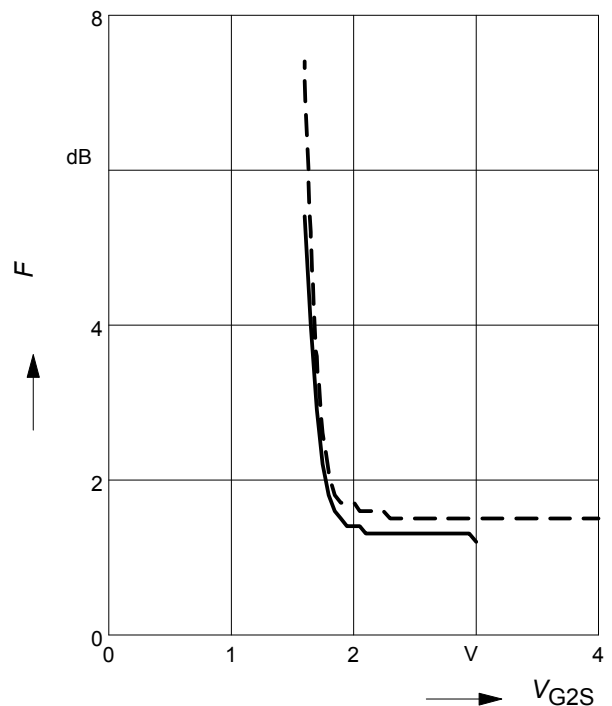
... $V_{DS} = 5$ V, $V_{G2S} = 4$ V, $R_{G1} = 180$ k Ω



Noise figure $F = f(V_{G2S}), f = 800$ MHz

— $V_{DS} = 3$ V, $V_{G2S} = 3$ V, $R_{G1} = 82$ k Ω

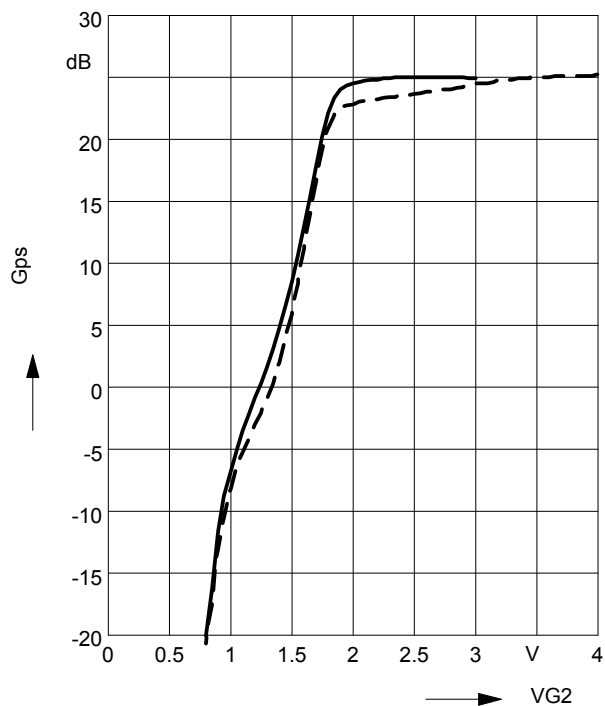
... $V_{DS} = 5$ V, $V_{G2S} = 4$ V, $R_{G1} = 180$ k Ω



Power gain $G_{ps} = f(V_{G2S})$, $f = 800$ MHz

— $V_{DS} = 3$ V, $V_{G2S} = 3$ V, $R_{g1} = 82$ k Ω

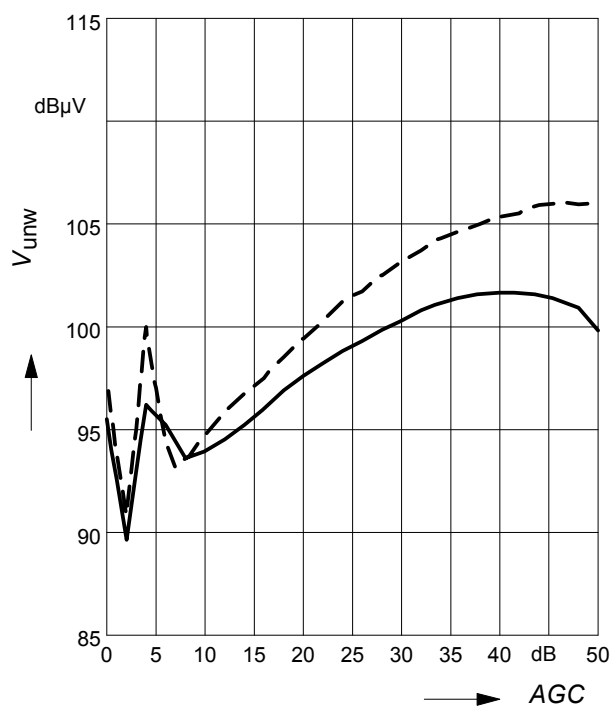
... $V_{DS} = 5$ V, $V_{G2S} = 4$ V, $R_{g1} = 180$ k Ω



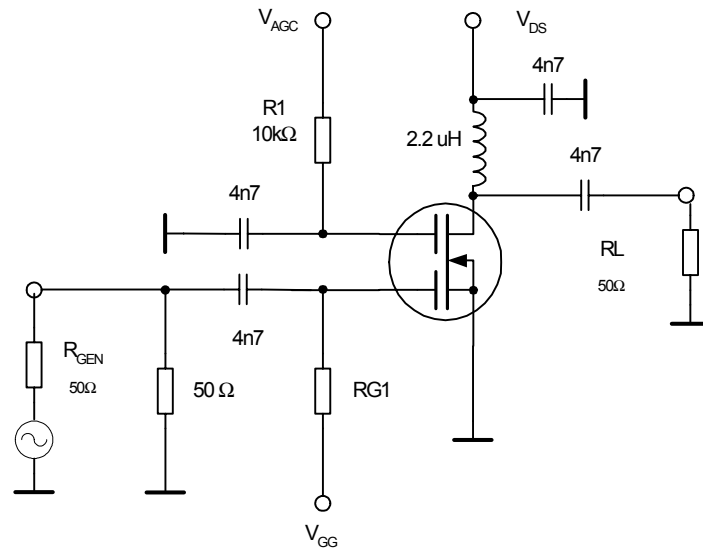
Crossmodulation $V_{unw} = (AGC)$

— $V_{DS} = 3$ V, $V_{G2S} = 3$ V, $R_{g1} = 82$ k Ω

... $V_{DS} = 5$ V, $V_{G2S} = 4$ V, $R_{g1} = 180$ k Ω



Crossmodulation test circuit



Semibiased

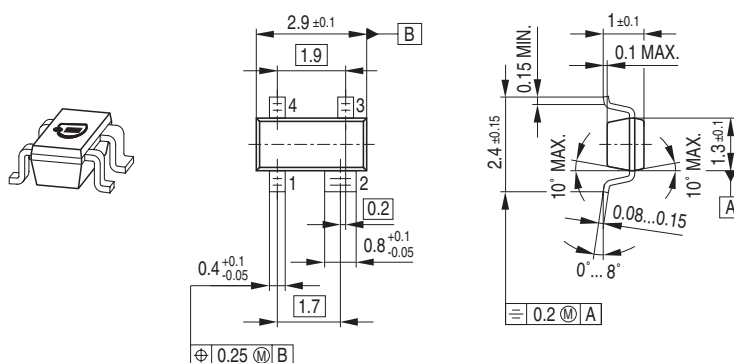
Technical drawing of a 4-pin D-sub connector. The drawing includes a perspective view of the connector on the left and two detailed cross-sectional views on the right. The left cross-section shows the internal structure with pins 1, 2, 3, and 4, and dimensions for the housing and pins. The right cross-section shows the contact area with dimensions for the contact thickness, contact angle, and contact width. The drawing is labeled with 'A' and 'B' for different views and includes a table of dimensions.

Symbol	Value	Unit
A	1.3 ± 0.1	mm
B	2.9 ± 0.1	mm
C	1.9	mm
D	0.2	mm
E	0.8 +0.1/-0.05	mm
F	0.4 +0.1/-0.05	mm
G	1.7	mm
H	0.25	mm
I	0.15 MIN.	mm
J	1 ± 0.1	mm
K	0.1 MAX.	mm
L	10° MAX.	°
M	10° MAX.	°
N	0.08...0.15	mm
O	0...8°	°
P	2.4 ± 0.15	mm
Q	0.2	mm

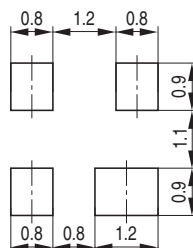
 Manufacturer
 RF S 56
 2005, June
Date code (YM)
 Pin 1
 BFP181
Type code

Technical drawing of a mechanical part, likely a bracket or support. The drawing includes a top view and a side view. The top view shows a rectangular base with a width of 4 and a height of 8. There are three rectangular slots along the bottom edge, each with a width of 3.15 and a height of 2.6. A pin is located at the bottom left corner, labeled "Pin 1". The side view shows a thickness of 0.2 and a height of 1.15.

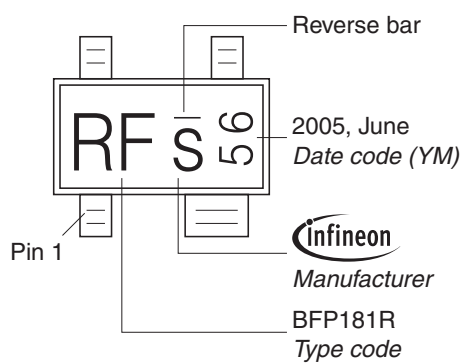
Package Outline



Foot Print

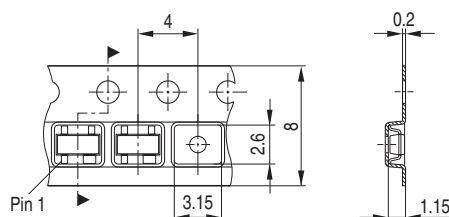


Marking Layout (Example)

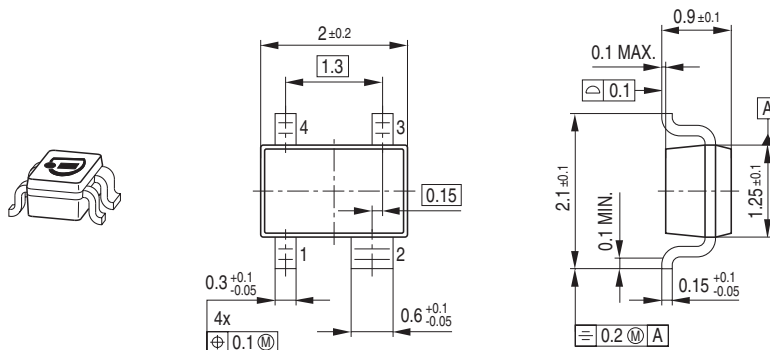


Standard Packing

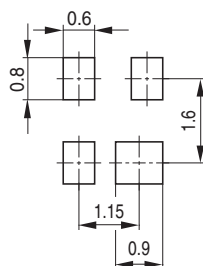
Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



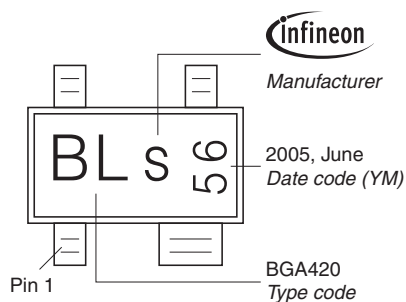
Package Outline



Foot Print

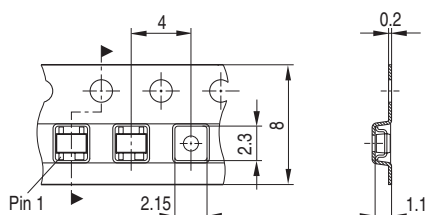


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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